

IN THE CLAIMS:

Please amend claims 17, 24 and 25 as follows:

LISTING OF CURRENT CLAIMS

Claims 1-16. (Canceled)

17. (Currently Amended) A semiconductor build-up package comprising:
 - a) a die having an active surface, a passive surface, and sides between the active surface and the passive surface;
 - b) a plurality of bonding pads electrically connected to the active surface of the die;
 - c) a metal carrier made only of metal and having a cavity in a top surface, the die being positioned within the cavity such that the passive surface and sides are within the cavity; and
 - d) a plurality of dielectric layers formed on the active surface of the die and the top surface of the metal carrier, each plurality of dielectric layers having a plurality of conductive columns electrically connected to the bonding pads of the die and a plurality of conductive traces electrically connecting corresponding conductive columns of one plurality of dielectric layers to corresponding conductive columns of another plurality of dielectric layers.
18. (Previously Presented) The semiconductor build-up package according to Claim 17, wherein the plurality of dielectric layers includes three dielectric layers.
19. (Previously Presented) The semiconductor build-up package according to Claim 17, wherein the die being positioned within the cavity such that the active surface of the die is coplanar with the top surface of the metal carrier.

20. (Previously Presented) The semiconductor build-up package according to Claim 17, wherein at least one of the plurality of conductive columns of each plurality of dielectric layers is vertically connected to at least one of the plurality of conductive columns of an adjacent plurality of dielectric layers.
21. (Previously Presented) The semiconductor build-up package according to Claim 17, further comprising a plurality of conductive pads, wherein one of the plurality of conductive pads is electrically connected to one of the plurality of conductive columns on the outer most plurality of dielectric layers.
22. (Previously Presented) The semiconductor build-up package according to Claim 21, further comprising a plurality of connectors selected from the group consisting of solder balls, bumps, and pins, wherein one of the plurality of connectors is electrically connected to each of the plurality of conductive pads.
23. (Previously Presented) The semiconductor build-up package according to Claim 21, wherein the plurality of conductive pads are arranged to form a grid array.
24. (Currently Amended) The semiconductor build-up package according to Claim 17, wherein the plurality of dielectric layers ~~being~~ are made from a dielectric material selected from the group consisting of polyimide, epoxy, BT resin, FR-4 resin, FR-5 resin, benzo cyclobutene (BCB), and polytetrafluoroethylene (PTFE).
25. (Currently Amended) The semiconductor build-up package according to Claim 17, wherein the metal carrier ~~being~~ is made from a metal selected from the group consisting of aluminum, aluminum alloy, copper, and copper alloy.

26. (Previously Presented) The semiconductor build-up package according to Claim 17, wherein the plurality of conductive columns are made from a metal material selected from the group consisting of aluminum, aluminum alloy, copper, and copper alloy.
27. (Previously Presented) The semiconductor build-up package according to Claim 17, wherein the metal carrier covers the passive surface and the sides of the die.